## Crystal Anisotropy in Surface Energy Engineering (SEE) of LiTaO<sub>3</sub>(110) Piezo-Electric for Low Temperature (< 453 K) Nano-Bonding<sup>TM</sup> to Si and α-Quartz SiO<sub>2</sub>

S. Prakash, M. Sahal, A.Elison, <u>Shrevash Prakash</u>, B. R. Baker, S. Narayan, L. M. Puglisi, R.J. Culbertson, N. Herbots ARIZONA STATE UNIVERSITY, *Department of Physics*, SIO<sub>2</sub> INNOVATES, LLC, ACCUANGLE ANALYTICS, LLC, Tempe, AZ

**<u>GOAL</u>**: This project's goal is to bond *anisotropic* LiTaO<sub>3</sub> to Si via Nano-Bonding<sup>TM, 1-2</sup>, which aims to minimizes thermal stress during bonding and maximizes density molecular cross-bonds via Surface Energy Engineering (SEE). SEE planarizes surfaces at three length scales to achieve direct "nano– contact", at the nano-, micro-, and macro-scale. SEE uses Three Liquid Contact Angle Analysis (3LCAA) and the van Oss-Chaudhury-Good theory to measure hydro-affinity (HA) and surface energies ( $\gamma^{T}$ ). These indicate the degree of interaction between surfaces. 3LCAA can map  $\gamma^{T}$  along different crystal orientations, thus detecting the effect of LiTaO<sub>3</sub>'s anisotropy on SEE and Nano-Bonding<sup>TM</sup>.

## EXPERIMENTAL RESULTS OF NANO-BONDING<sup>TM</sup> LITAO<sub>3</sub> to SI:

Hydrophobic LiTaO<sub>3</sub> nano-bonds at RT in air to hydrophilic SiO<sub>2</sub><sup>2</sup>. During nano-contacting, the nanobonded area increases over time, but the bonding is non-uniform<sup>2</sup> as shown in **Fig.1**. **Time (s)** *Initial Nano-Contact* 0 157 221 267



Fig. 1 Optical obsvervation of nano-bonded area between  $LiTaO_3$  and  $\alpha$ -Quartz SiO<sub>2</sub> changing over time.

<u>**QUANTIFYING THE ROLE OF ANISOTROPY**</u>: To understand how LiTaO<sub>3</sub>'s anisotropy plays a role in Nano-Bonding<sup>TM</sup> of LiTaO<sub>3</sub> to Si, elliptical distortion of the 3LCAA drops is measured in addition to water contact angle ( $\theta_{H2O}$ ) and Surface Energy ( $\gamma^{T}$ ) as a function of crystal orientation, as shown in **Fig.2**.



Fig.2 (a) and (b)  $\theta_{H2O}$  mapping across 15 crystal planes intersecting LiTaO<sub>3</sub> before SEE.

**Fig. 2** (a) shows  $\theta_{H2O}$  mapping across 15 crystal planes intersecting LiTaO<sub>3</sub> before SEE. This shows that  $\theta_{H2O}$  varies significantly, by 40%, with crystal direction when mapped across a 150 mm (6") LiTaO<sub>3</sub> (100)

wafer diameter. It averages  $45 \pm 5.4^{\circ}$  along <0001> direction intersecting the (110) surface plane, with a range, R, of  $17 \pm 1^{\circ}$ . This is a significant variation as R is >  $3\sigma = 3 \times 5.4^{\circ} = 16.2^{\circ}$ . The Miller indices of the crystal planes in (a) intersecting the location where each of the eighteen  $\theta_{H20}$  are measured, are listed and (b) depicts how measured  $\theta_{H20}$  correlates to crystal direction.  $\theta_{H20}$  is measured four times for the (-4,4,-1) plane, averaging  $48.1 \pm 1.8^{\circ}$ , and the (-2,2,1) plane, averaging  $41.3 \pm 1.6^{\circ}$ . This shows that with 4 data points, the experimental error is  $1.7^{\circ}$  for these two planes, 10 x less than the measured range R.



Fig. 3 Comparison of water contact angle  $\theta_{H2O}$  mapped across (a) LiTaO<sub>3</sub> (b) Si, and (c)  $\alpha$ -Quartz SiO<sub>2</sub> wafers highlighting the uniformity of  $\theta_{H2O}$  on Si and  $\alpha$ -Quartz SiO<sub>2</sub> versus the non-uniformity LiTaO<sub>3</sub>.

**Fig.3** compares  $\theta_{H2O}$ 's mapped across (**a**) 6" LiTaO<sub>3</sub> (110) along <0001> (**b**) 6" Si (100), and (**c**)  $\alpha$ -Quartz SiO<sub>2</sub> (100). Si and SiO<sub>2</sub> exhibit much more uniform  $\theta_{H2O}$  mapping than LiTaO<sub>3</sub> by at least a full order of magnitude. LiTaO<sub>3</sub>'s intersecting crystal planes each represents a uniquely different chemical arrangement of atoms and stochiometric composition of elements, affecting the surface dipole and  $\gamma^{T}$  at each location on LiTaO<sub>3</sub> (110). In comparison, cubic Si (100) and almost cubic piezoelectric  $\alpha$ -Quartz SiO<sub>2</sub> (which has also a trigonal like LiTaO<sub>3</sub>, but with much closer a,b,c, lattice constants) don't have very different chemical structures based off of location on wafer, thus resulting in much more  $\theta_{H2O}$  uniformity.



**Fig. 4** Mapping of total surface energy  $(\gamma^T)$  and its components  $(\gamma^{LW}, \gamma^+, \gamma^-)$ , at each water drop position on the LiTaO<sub>3</sub> wafer.  $\gamma^T$  varies by  $\pm 6\%$ , which is significantly less than the 40% variation of  $\theta_{H2O}$ .

**Fig. 4** shows that the variations in the electron acceptor  $\gamma^{T}$  and electron donor  $\gamma^{+}$  cancel each other out, thus resulting in a rather uniform  $\gamma^{T}$ .